

## ABSTRACT OF THE DISCLOSURE

In the fabricating of a light emitting device, a light emitting  
5 layer portion 24 and a current spreading layer 7, respectively  
composed of a Group III-V compound semiconductor, are stacked on a  
single crystal substrate. The light emitting layer portion 24 is  
formed by a metal organic vapor-phase epitaxy process, and the  
current spreading layer 7, on such light emitting layer portion 24,  
10 is formed to have conductivity type of n-type by a hydride vapor-  
phase epitaxy process.